

## SOT23 N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

### Features

• For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.

<u>https://www.diodes.com/quality/product-definitions/</u>

PARTMARKING DETAIL – SA

## Absolute Maximum Ratings



PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V <sub>DS</sub>	100	V
Drain-Gate Voltage	V <sub>DGR</sub>	100	V
Continuous Drain Current at T <sub>amb</sub> =25°C	I <sub>D</sub>	170	mA
Pulsed Drain Current	I <sub>DM</sub>	680	mA
Gate-Source Voltage	V <sub>GS</sub>	± 20	V
Peak Gate-Source Voltage	V <sub>GSM</sub>	± 20	V
Power Dissipation at T <sub>amb</sub> =25°C	P <sub>tot</sub>	360	mW
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

PARAMETER	SYMBOL	MIN.	MIN.	MAX.	UNIT	CONDITIONS.	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100			V	I <sub>D</sub> =0.25mA, V <sub>GS</sub> =0V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	0.8	2.2	2.8	V	I <sub>D</sub> =1mA, V <sub>DS</sub> = V <sub>GS</sub>	
Gate-Body Leakage	I <sub>GSS</sub>		10	50	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		1 2	15 60 10	μΑ μΑ nA	$V_{DS}$ =100V, $V_{GS}$ =0V $V_{DS}$ =100V, $V_{GS}$ =0V, T=125°C(2) $V_{DS}$ =20V, $V_{GS}$ =0V	
Static Drain-Source On-State Resistance (1)	R <sub>DS(on)</sub>		5	6	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =100mA	
Forward Transconductance(1)(2)	9 <sub>fs</sub>	80	120		mS	V <sub>DS</sub> =25V, I <sub>D</sub> =100mA	
Input Capacitance (2)	C <sub>iss</sub>			20	pF		
Common Source Output Capacitance (2)	C <sub>oss</sub>			9	pF	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	
Reverse Transfer Capacitance (2)	C <sub>rss</sub>			4	pF		
Turn-On Delay Time (2)(3)	t <sub>d(on)</sub>		10		ns		
Rise Time (2)(3)	t <sub>r</sub>		10		ns	$V_{DD} \approx 30V, I_{D} = 280 mA$	
Turn-Off Delay Time (2)(3)	t <sub>d(off)</sub>		15		ns		
Fall Time (2)(3)	t <sub>f</sub>		25		ns		

(1) Measured under pulsed conditions. Width=300µs. Duty cycle ≤2% (2) Sample test.

(3) Switching times measured with  $50\Omega$  source impedance and <5ns rise time on a pulse generator

For typical characteristics graphs see ZVN3310F datasheet.



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